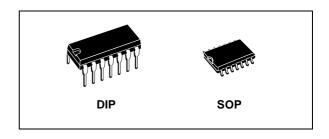


HCF4066B

QUAD BILATERAL SWITCH FOR TRANSMISSION OR MULTIPLEXING OF ANALOG OR DIGITAL SIGNALS

- 15V DIGITAL OR ± 7.5V PEAK TO PEAK SWITCHING
- 125Ω TYPICAL ON RESISTANCE FOR 15V OPERATION
- SWITCH ON RESISTANCE MATCHED TO WITHIN 5Ω TYP. OVER 15V SIGNAL INPUT RANGE
- ON RESISTANCE FLAT OVER FULL PEAK TO PEAK SIGNAL RANGE
- HIGH ON/OFF OUTPUT VOLTAGE RATIO: 65dB TYP. at $f_{IS} = 10$ KHz, $R_L = 10$ K Ω
- HIGH DEGREE OF LINEARITY: < 0.5% DISTORTION TYP. at $f_{IS} = 1 \text{KHz}$, $V_{IS} = 5 \text{ V}_{pp}$, $V_{DD} V_{SS} \ge 10 \text{V}$, $RL = 10 \text{K}\Omega$
- EXTREMELY LOW OFF SWITCH LEAKAGE RESULTING IN VERY LOW OFFSET CURRENT AND HIGH EFFECTIVE OFF RESISTANCE: 10pA TYP. at V_{DD} V_{SS} = 10V, T_{amb} = 25°C
- EXTREMELY HIGH CONTROL INPUT IMPEDANCE (control circuit isolated from signal circuit 10¹²Ω typ.)
- LOW CROSSTALK BETWEEN SWITCHES: 50dB Typ. at $f_{IS} = 0.9 MHz$, $R_{I} = 1 K\Omega$
- MATCHED CONTROL INPUT TO SIGNAL OUTPUT CAPACITANCE: REDUCES OUTPUT SIGNAL TRANSIENTS
- FREQUENCY RESPONSE SWITCH ON: 40MHz (Typ.)
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS



ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4066BEY	
SOP	HCF4066BM1	HCF4066M013TR

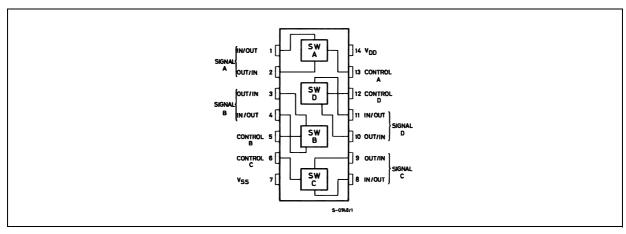
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT

DESCRIPTION

The HCF4066B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4066B is a QUAD BILATERAL SWITCH intended for the transmission or multiplexing of analog or digital signals.

It is pin for pin compatible with HCF4016B, but exhibits a much lower ON resistance. In addition, the ON resistance is relatively constant over the full input signal range. The HCF4066B consists of four independent bilateral switches. A single control signal is required per switch. Both the p

PIN CONNECTION

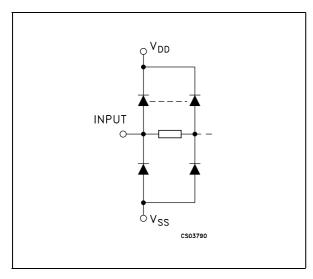


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and n device in a given switch are biased ON or OFF simultaneously by the control signal. As shown in schematic diagram, the well of the n-channel device on each switch is either tied to the input when the switch is ON or to V_{SS} when the switch is OFF. This configuration eliminates the variation of the switch-transistor threshold voltage with input signal, and thus keeps the ON resistance low over the full operating signal range. The advantages over single channel switches

include peak input signal voltage swings equal to the full supply voltage, and more constant ON impedance over the input signal range. For sample and hold applications, however, the HCF4016B is recommended.

INPUT EQUIVALENT CIRCUIT



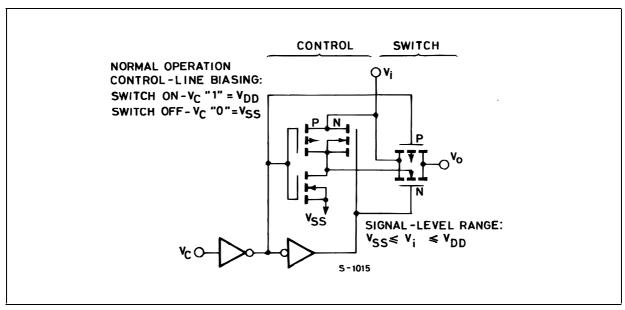
PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1, 4, 8, 11	A to D I/O	Independent Inputs/Outputs
2, 3, 9, 10	A to D O/I	Independent Outputs/ Inputs
13, 5, 6, 12	CONTROL A to D	Enable Inputs
7	V _{SS}	Negative Supply Voltage
14	V_{DD}	Positive Supply Voltage

TRUTH TABLE

CONTROL	SWITCH FUNCTION
Н	ON
L	OFF

 $\begin{array}{l} \textbf{SCHEMATIC DIAGRAM} \text{ (1 OF 4 IDENTICAL SWITCHES AND ITS ASSOCIATED CONTROL} \\ \textbf{CIRCUITY)} \end{array}$



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to $V_{\mbox{SS}}$ pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C

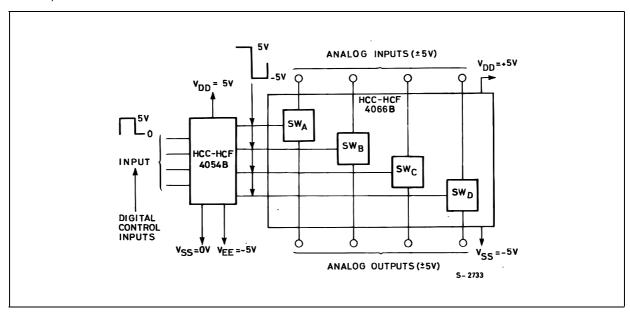
ELECTRICAL CHARACTERISTICS

 $(T_{amb} = 25$ °C, Typical temperature coefficient for all V_{DD} value is 0.3%/°C)

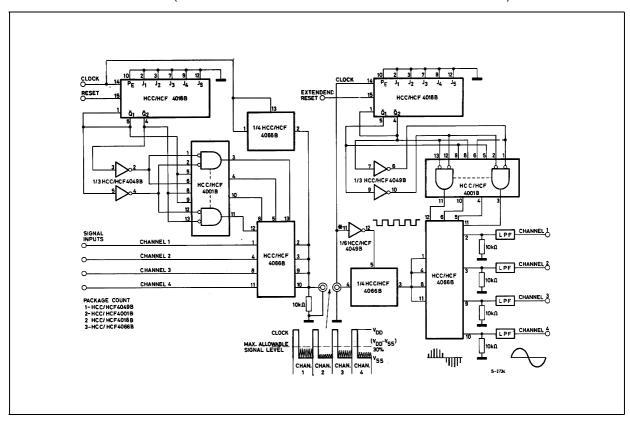
		Test Condition		Value								
Symbol	Parameter		VI	V _{DD}	T _A = 25°C		-40 to 85°C		-55 to 125°C		Unit	
			(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Device		0/5	5		0.01	0.25		7.5		7.5	
	Current (all		0/10	10		0.01	0.5		15		15	
	switches ON or all switches OFF)		0/15	15		0.01	1		30		30	μΑ
	SWITCH OF OT 1)		0/20	20		0.02	5		150		150	
SIGNAL	INPUTS (V _{IS}) and O	UTPUTS (V _{OS})										
R _{ON}	Resistance	$V_C = V_{DD} R_L = 1$	0ΚΩ	5		470	1050		1200		1200	
		Return to (V _{DD} -\	/ _{SS})/2	10		180	400		500		500	Ω
		$V_{IS} = V_{SS}$ to V_{IS}	_{DD}	15		125	240		300		300	
Δ_{ON}	Resistance Δ_{RON}			5		5						
	(between any 2 of	$R_L = 10K\Omega, V_C =$	= V _{DD}	10		10						Ω
	4 switches)			15		15						
TDH	Total Harmonic Distortion	$V_C = V_{DD} = 5V$, $V_{SS} = -5V$ V_{IS} (p-p) = 5V, $R_L = 10K\Omega$ (sine wave centered in 0V) $f_{IS} = 1KHz$ sine wave			0.4						%	
	-3dB Cutoff Frequency (Switch on)	$V_C = V_{DD} = 5V$ $V_{IS} (p-p) = 5V$ (sine wave cen	, R _L =	1ΚΩ		40						MHz
	-50dB Feedthrough Frequency (switch off)	$V_C = V_{SS}$ $V_{IS} (p-p) = 5V_{IS}$ (sine wave cen	, R _L =			1						MHz

		Test Condition	Value								
Symbol Parame	Parameter	V _I	V _{DD}	T _A = 25		С	-40 to 85°C		-55 to 125°C		Unit
		(v)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
	-50dB Crosstalk Frequency	$V_{C(A)} = V_{DD} = +5$ $V_{C(B)} = V_{SS} = -5$ $V_{IS(A)} = 5V (p-p)$ 50Ω source, $R_L = 1$	V		8						MHz
t _{pd}	Propagation Delay	$R_L = 200K\Omega, V_C = V$			20	40					
	Time (signal input to output)	$V_{SS} = GND, C_L = 5$	0pF		10	20					
	to output)	V_{IS} = 10V square wave centered t_{r} , t_{f} = 20ns	on 5V		7	15					ns
C _{IS}	Input Capacitance				8						
C _{OS}	Output Capacitance	$V_C = V_{SS} = -5$	+5		8						pF
C _{IOS}	Feedthrough				0.5						
	Input/Output Leakage Current Switch OFF	$V_{C} = 0V$ $V_{IS} = 18V, V_{OS} = 0V$ $V_{IS} = 0V, V_{OS} = 18V$	18		±10 ⁻³	±0.1		±1		±1	μΑ
CONTRO	DL (V _C)	-	ı	ı		I	I				ı
V _{ILC}	Control Input Low		5			1		1		1	
	Voltage	I _{IS} < 10 μA	10			2		2		2	V
.,	0 1 1 1 1 1	$V_{IS} = V_{SS}, V_{OS} = V_{DD}$	15	0.5		2	0.5	2	0.5	2	
V_{IHC}	Control Input High Voltage	V _{IS} = V _{DD} , V _{OS} = V _{SS}	5 10	3.5 7			3.5 7		3.5 7		V
		115 100, 105 155	15	11			11		11		v
II	Input Leakage Current	$V_{IS} \le V_{DD}$ $V_{DD} - V_{SS} = 18V$	18		±10 ⁻⁵	±0.1		±1		±1	μА
	Crosstalk (control input to signal output)	V_C = 10V (sq. wave) t_r , t_f = 20ns R_L = 10KΩ	10		50						mV
	Turn - On	$V_{IN} = V_{DD,} t_r, t_f = 20 \text{ns}$	5		35	70					
	Propagation Delay Time	$C_1 = 50 \text{pF}, R_1 = 1 \text{K}\Omega$	10		20	40					ns
			15		15	30					
	Control Input Repetition Rate	$V_{IS}=V_{DD}, V_{SS}=GND$ $R_L = 1K\Omega$ to GND	5 10		6 9			<u> </u>	-		
		$C_L = 50pF$, $V_C = 10V$ $c_L = 50pF$, $V_C = 10V$	15		9.5						MHz
C _I	Input Capacitance	Any Input			5	7.5					pF

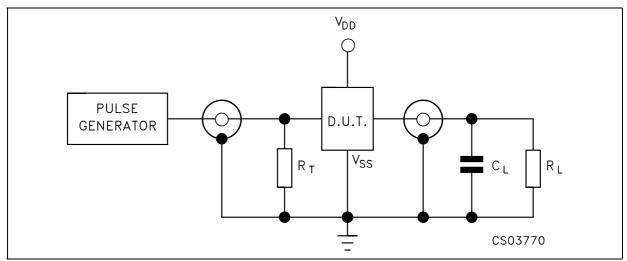
TYPICAL APPLICATIONS (BIDIRECTIONAL SIGNAL TRANSMISSION VIA DIGITAL CONTROL LOGIC)



TYPICAL APPLICATIONS (4-CHANNEL PAM MULTIPLEXER SYSTEM DIAGRAM)

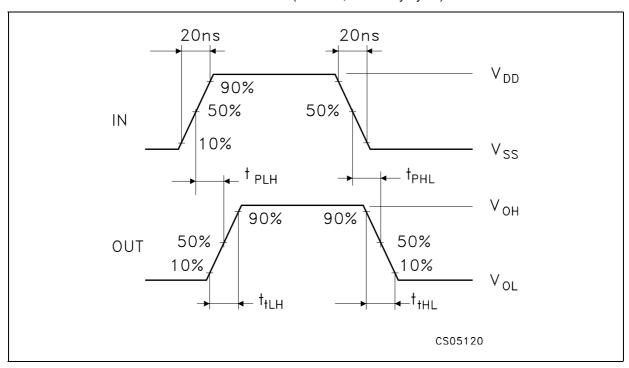


TEST CIRCUIT



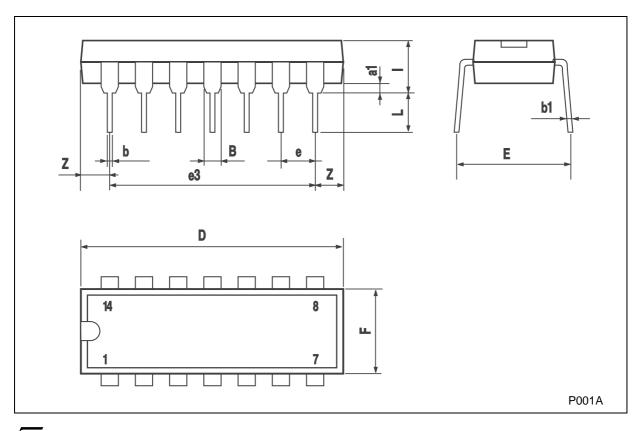
 C_L = 50pF or equivalent (includes jig and probe capacitance) R_L = 200K Ω R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



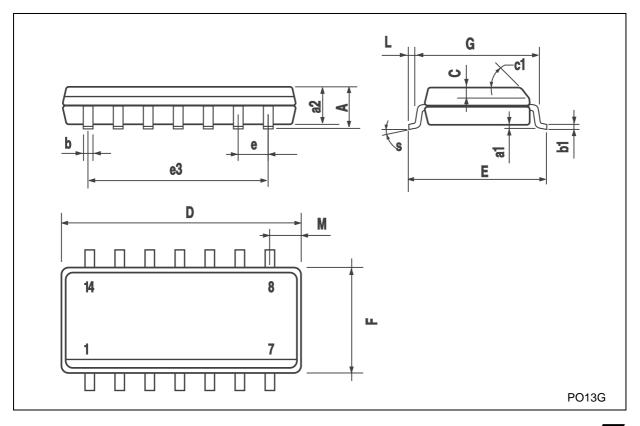
Plastic DIP-14 MECHANICAL DATA

DIM	mm.					
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



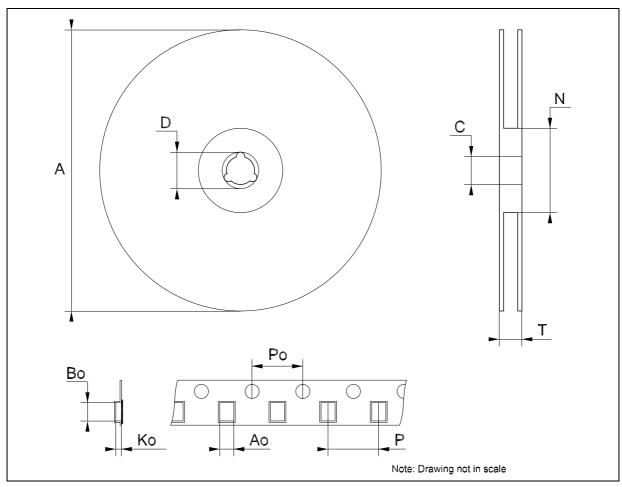
SO-14 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1		1	45°	(typ.)		•
D	8.55		8.75	0.336		0.344
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.68			0.026
S			8° (r	max.)		•



Tape &	Reel	SO-14	MECHA	NICAL	DATA
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DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
Т			22.4			0.882
Ao	6.4		6.6	0.252		0.260
Во	9		9.2	0.354		0.362
Ко	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
Р	7.9		8.1	0.311		0.319



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